TOSHIBA GTR Module Silicon N Channel IGBT

MG150J7KS50

High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- 7 IGBTs built into 1 package.
- Enhancement-mode
- High speed type IGBT: Inverter stage

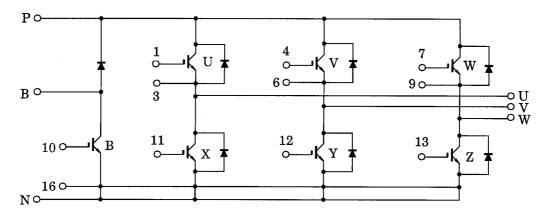
: $V_{CE \text{ (sat)}} = 2.8V \text{ (max)} \text{ (@IC} = 150A)$

: $t_f = 0.5 \mu s \text{ (max) (@IC} = 150 A)$: $t_{rr} = 0.3 \mu s \text{ (max) (@IF} = 150 A)$

• Outline : TOSHIBA 2-110A1B

• Weight: 520g

Equivalent Circuit



Signal Terminal

1 : G (U)	2 : Open	3 : E(U)	4 : G (V)
5 : Open	$6 : \mathbf{E}(\mathbf{V})$	7 : G (W)	8 : Open
9 : E(W)	10: G(B)	11:G(X)	12:G(Y)
13:G(Z)	14 : Open	15 : Open	16 : E

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2001-08-16

Inverter Stage

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Callantar assument	DC	IC	150	Α	
Collector current	1ms	I _{CP}	300	A	
Forward current	DC	IF	150	Α	
Forward current	1ms	I _{FM}	300	_ ^	
Collector power dissipation (Tc = 25°C)		PC	320	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	- 40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±500	nA
Collector-emitter cut-off current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	V _{CE} = 5V, I _C = 15mA,	5.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 150A, V _{GE} = 15V	_	2.2	2.8	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	_	12.0	_	nF
Forward voltage		V _F	I _F = 150A	_	2.5	3.5	V
	Rise time	t _r	Inductive load	_	0.15	0.3	
	Turn-on time	t _{on}	V _{CC} = 300V	_	0.23	0.46	
Switching time	Fall time	t _f	I _C = 150A V _{GE} = ±15V	_	0.25	0.50	μs
	Turn-off time	t _{off}	$R_G = 9.2\Omega$	_	0.50	1.00	
	Reverse recovery time	trr	(Note 1)	_	0.15	0.30	
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	0.39	
			Diode stage	_	_	1.00	°C/W
		R _{th (c-f)}	Case to fin (Note 2)	_	0.05	_	

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Note 2: Silicone grease is applied.

Brake Stage

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Reverse voltage		V_{R}	600	V	
Collector current	DC	I _C	50	Α	
	1ms	I _{CP}	100	A	
Forward current	DC	I _F	50	Α	
	1ms	I _{FM}	100	A	
Collector power dissipation (Tc = 25°C)		PC	120	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

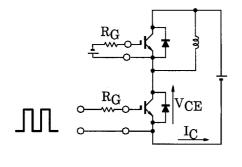
Electrical Characteristics (Ta = 25°C)

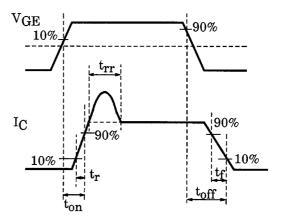
Characteristics		Symbol	Test Condition	Min	Тур.	Max	UNIT
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0V	_	_	±500	nA
Collector-emitter cut-off current		I _{CES}	V _{CE} = 600V, V _{GE} = 0V		_	1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	V _{CE} = 5V, I _C = 5mA,	5.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 50A, V _{GE} = 15V		2.0	2.5	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		4.0	_	nF
Reverse current		I _R	V _R = 600V		_	1.0	mA
Forward voltage		V _F	I _F = 150A		2.2	2.8	V
	Rise time	t _r	Inductive load		0.08	0.16	
	Turn-on time	t _{on}	V _{CC} = 300V	1	0.10	0.20	
Switching time	Fall time	t _f	I_C = 50A V_{GE} = ±15V R_G = 24 Ω (Note 1)	1	0.22	0.44	μs
	Turn-off time	t _{off}			0.50	1.00	
	Reverse recovery time	trr			0.23	0.35	
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	1.04	
			Diode stage	_	_	2.00	°C/W
		R _{th (c-f)}	Case to fin (Note 2)	_	0.05	_	

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Note 2: Silicone grease is applied.

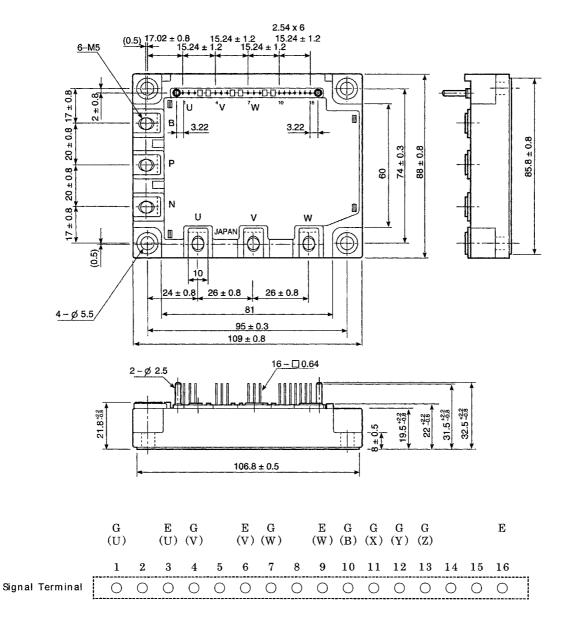
Note 1: Switching Time Test Circuit & Timing Chat





Package Dimensions

TOSHIBA 2-110A1B Unit: mm



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